High Voltage Transistors

NPN Silicon

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT5550 MMBT5551	V _{CEO}	140 160	Vdc
Collector – Base Voltage MMBT5550 MMBT5551	V _{CBO}	160 180	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	600	mAdc
Electrostatic Discharge Human Body Model Machine Model	ESD	> 8000 > 400	٧

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate Above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T _A = 25°C Derate Above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

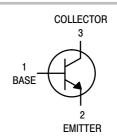
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



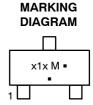
ON Semiconductor®

http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 6



x1x = Device Code

M1F = MMBT5550LT

G1 = MMBT5551LT

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5550LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5551LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			-	-	
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT5550 MMBT5551	V _{(BR)CEO}	140 160	_ _	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	MMBT5550 MMBT5551	V _{(BR)CBO}	160 180	- -	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	6.0	_	Vdc
Collector Cutoff Current	MMBT5550 MMBT5551 MMBT5550 MMBT5551	Ісво	- - - -	100 50 100 50	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)		I _{EBO}	-	50	nAdc
ON CHARACTERISTICS					
DC Current Gain $(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5550 MMBT5551 MMBT5550 MMBT5551 MMBT5550 MMBT5551	h _{FE}	60 80 60 80 20 30	- 250 250 - -	-
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	Both Types MMBT5550 MMBT5551	V _{CE(sat)}	- - -	0.15 0.25 0.20	Vdc
Base – Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	Both Types MMBT5550 MMBT5551	V _{BE(sat)}	- - -	1.0 1.2 1.0	Vdc
Collector Emitter Cut-off (V _{CB} = 10 V) (V _{CB} = 75 V)	Both Types	I _{CES}	_ _	50 100	nA

^{3.} Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

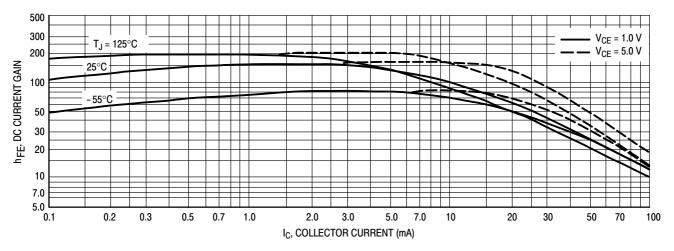


Figure 1. DC Current Gain

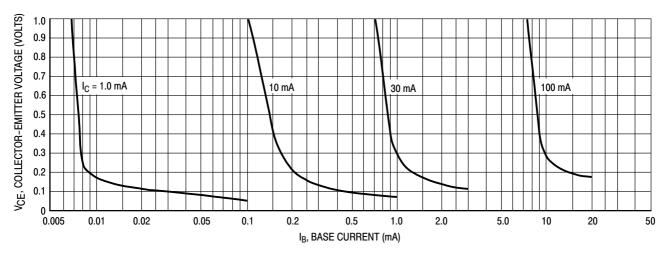


Figure 2. Collector Saturation Region

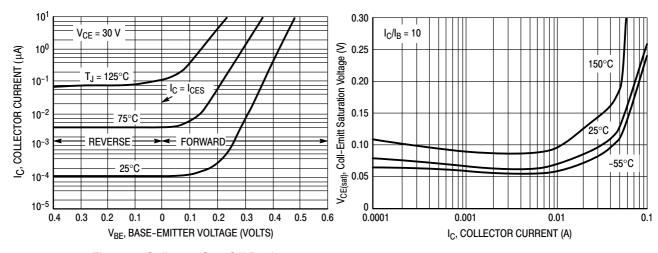


Figure 3. Collector Cut-Off Region

Figure 4. V_{CE(sat)}

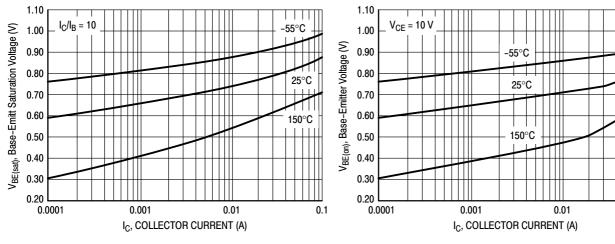


Figure 5. V_{BE(sat)}

Figure 6. V_{BE(on)}

0.1

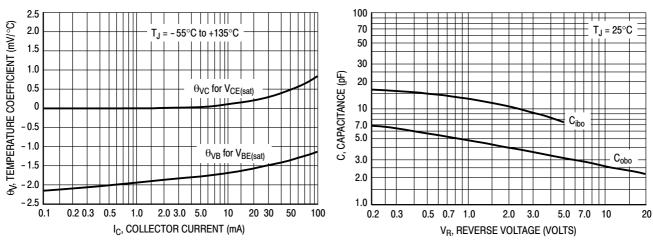
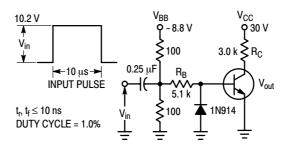


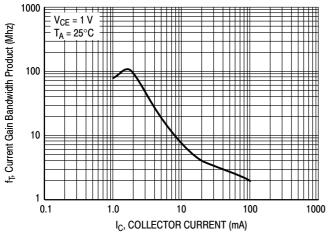
Figure 7. Temperature Coefficients

Figure 8. Capacitances



Values Shown are for I_C @ 10 mA

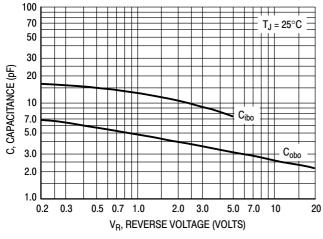
Figure 9. Switching Time Test Circuit



0.001 0.001 1.0 10 100 1000 V_{CE}, COLLECTOR EMITTER VOLTAGE (V)

Figure 10. Current Gain Bandwidth Product

Figure 11. Safe Operating Area





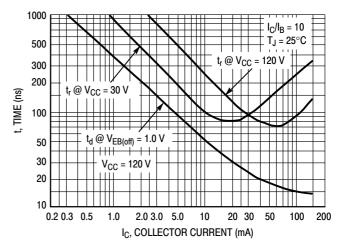
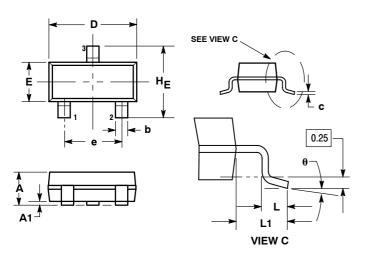


Figure 13. Turn-On Time

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 FM 1082
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

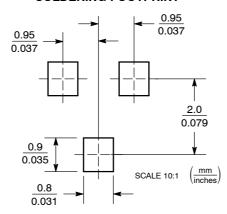
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

PIN 1. BASE

- 2. EMITTER
- 3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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